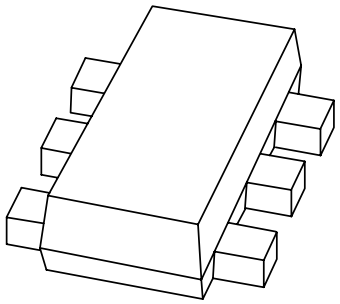
DATA SHEET



PEMZ7
NPN/PNP general purpose transistors

Product data sheet
Supersedes data of 2001 Sep 25

2001 Nov 07

NPN/PNP general purpose transistors PEMZ7

FEATURES

- 300 mW total power dissipation
- Very small 1.6 × 1.2 mm ultra thin package
- Self alignment during soldering due to straight leads
- Low collector capacitance
- Low V_{CEsat}
- High current capabilities
- Improved thermal behaviour due to flat leads
- Reduced required PCB area
- Reduced pick and place costs.

APPLICATIONS

- Heavy duty battery powered equipment (automotive, telecom and audio-video) such as motor and lamp drivers
- V_{CEsat} critical applications such as latest low supply voltage IC applications
- All battery driven equipment, to save battery power.

DESCRIPTION

NPN/PNP low V_{CEsat} transistor pair in a SOT666 plastic package.

MARKING

TYPE NUMBER	MARKING CODE
PEMZ7	Z7

PINNING

PIN	DESCRIPTION	
1, 4	emitter	TR1; TR2
2, 5	base	TR1; TR2
6, 3	collector	TR1; TR2

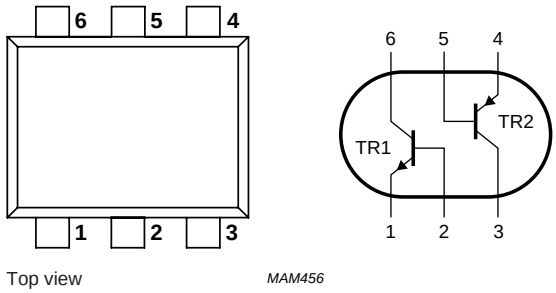


Fig.1 Simplified outline (SOT666) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transistor; for the PNP transistor with negative polarity					
V_{CBO}	collector-base voltage	open emitter	–	15	V
V_{CEO}	collector-emitter voltage	open base	–	12	V
V_{EBO}	emitter-base voltage	open collector	–	6	V
I_C	collector current (DC)		–	500	mA
I_{CM}	peak collector current		–	1	A
I_{BM}	peak base current		–	100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C; note 1	–	200	mW
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		−65	+150	°C
Per device					
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C; note 1	–	300	mW

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	notes 1 and 2	416	K/W

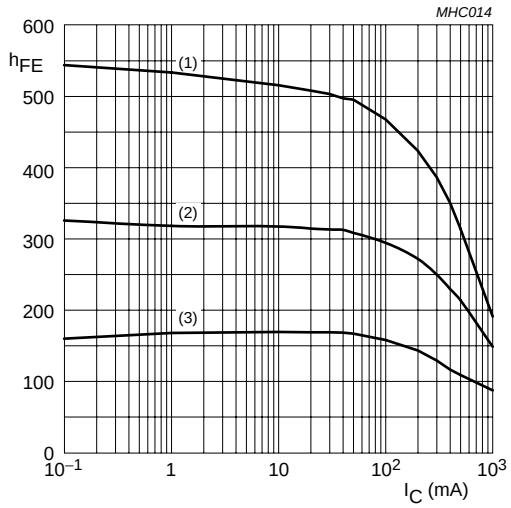
Notes

1. Transistor mounted on an FR4 printed-circuit board.
2. The only recommended soldering method is reflow soldering.

CHARACTERISTICS

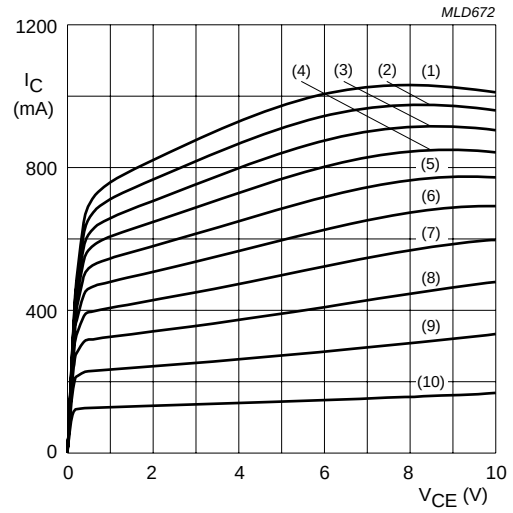
T_{amb} = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per transistor; for the PNP transistor with negative polarity						
I_{CBO}	collector-base cut-off current	V_{CB} = 15 V; I_E = 0	–	–	100	nA
		V_{CB} = 15 V; I_E = 0; T_j = 150 °C	–	–	50	μA
I_{EBO}	emitter-base cut-off current	V_{EB} = 5 V; I_C = 0	–	–	100	nA
h_{FE}	DC current gain	V_{CE} = 2 V; I_C = 10 mA	200	–	–	
V_{CEsat}	collector-emitter saturation voltage	I_C = 200 mA; I_B = 10 mA	–	–	220	mV
f_T	transition frequency	I_C = 100 mA; V_{CE} = 5 V; f = 100 MHz				
	TR1 (NPN)		250	420	–	MHz
	TR2 (PNP)		100	280	–	MHz
C_c	collector capacitance	V_{CB} = 10 V; I_E = I_e = 0; f = 1 MHz				
	TR1 (NPN)		–	4.4	6	pF
	TR2 (PNP)		–	–	10	pF



TR1 (NPN); V_{CE} = 2 V.
(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

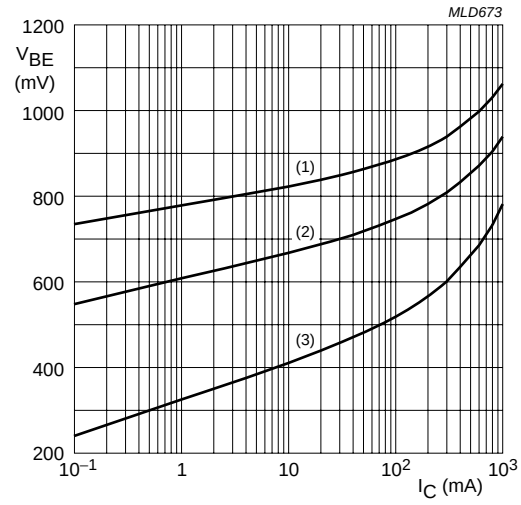
Fig.2 DC current gain as a function of collector current; typical values.



TR1 (NPN); T_{amb} = 25 °C.

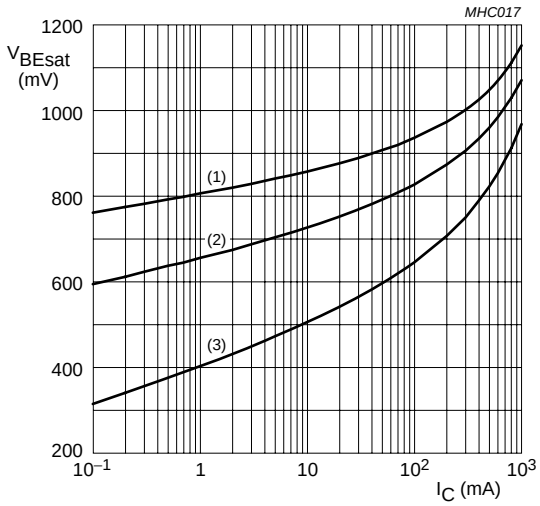
(1) I_B = 4.60 mA
(2) I_B = 4.14 mA
(3) I_B = 3.68 mA
(4) I_B = 3.22 mA
(5) I_B = 2.76 mA
(6) I_B = 2.30 mA
(7) I_B = 1.84 mA
(8) I_B = 1.38 mA
(9) I_B = 0.92 mA
(10) I_B = 0.46 mA

Fig.3 Collector current as a function of collector-emitter voltage; typical values.



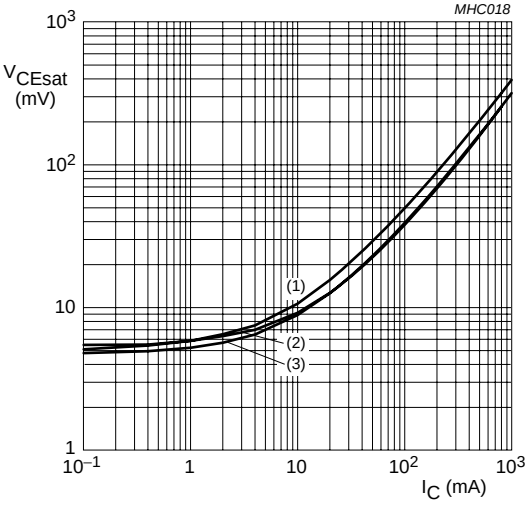
TR1 (NPN); V_{CE} = 2 V.
(1) T_{amb} = −55 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 150 °C.

Fig.4 Base-emitter voltage as a function of collector current; typical values.



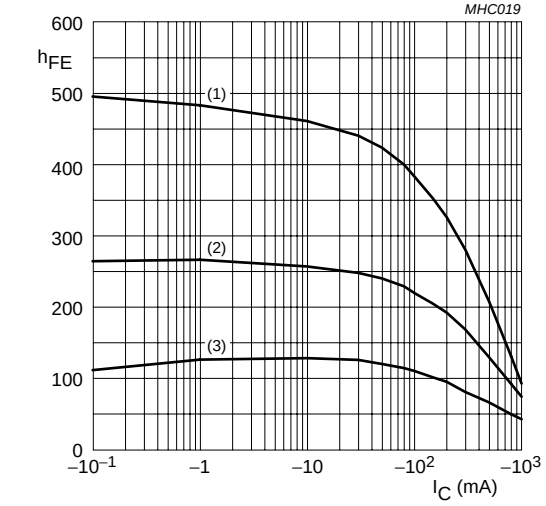
TR1 (NPN); I_C/I_B = 20.
(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.



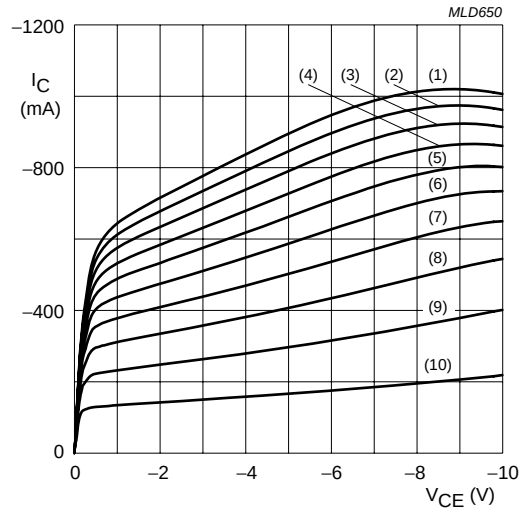
TR1 (NPN); I_C/I_B = 20.
(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

Fig.6 Collector-emitter saturation voltage as a function of collector current; typical values.



TR2 (PNP); V_{CE} = −2 V.
(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

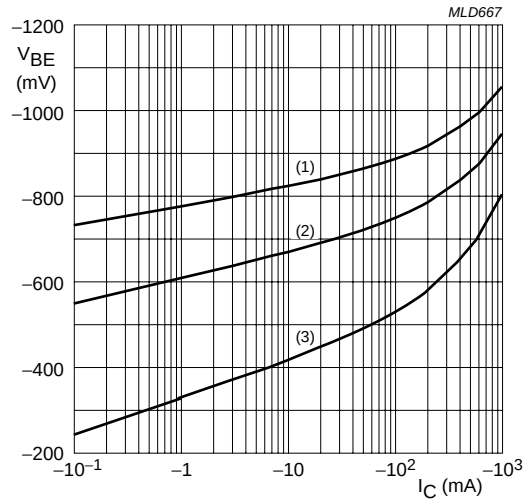
Fig.7 DC current gain as a function of collector current; typical values.



TR2 (PNP); T_{amb} = 25 °C.

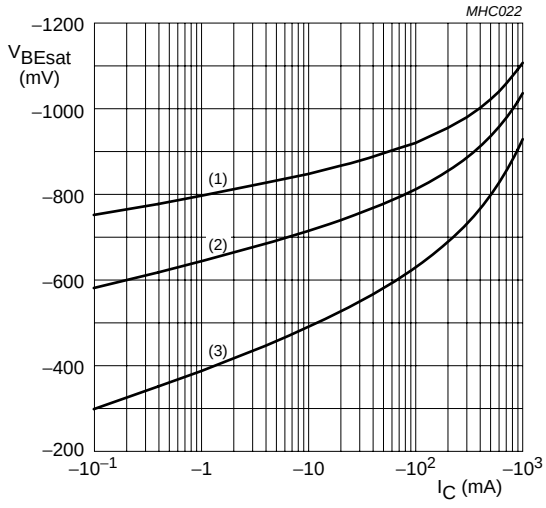
(1) I_B = 7.0 mA
(2) I_B = 6.3 mA
(3) I_B = 5.6 mA
(4) I_B = 4.9 mA
(5) I_B = 4.2 mA
(6) I_B = 3.5 mA
(7) I_B = 2.8 mA
(8) I_B = 2.1 mA
(9) I_B = 1.4 mA
(10) I_B = 0.7 mA

Fig.8 Collector current as a function of collector-emitter voltage; typical values.



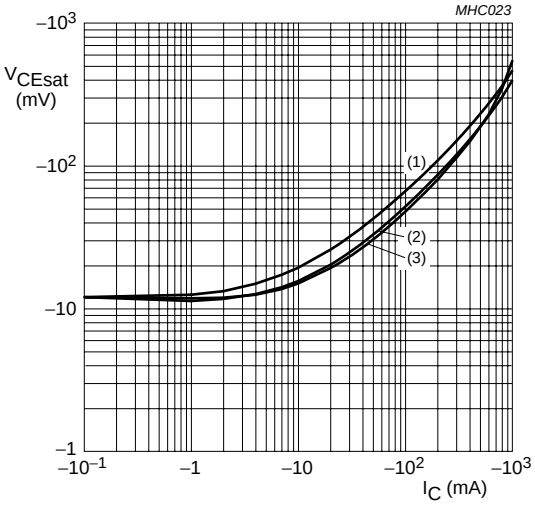
TR2 (PNP); V_{CE} = −2 V.
(1) T_{amb} = −55 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 150 °C.

Fig.9 Base-emitter voltage as a function of collector current; typical values.



TR2 (PNP); I_C/I_B = 20.
(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

Fig.10 Base-emitter saturation voltage as a function of collector current; typical values.

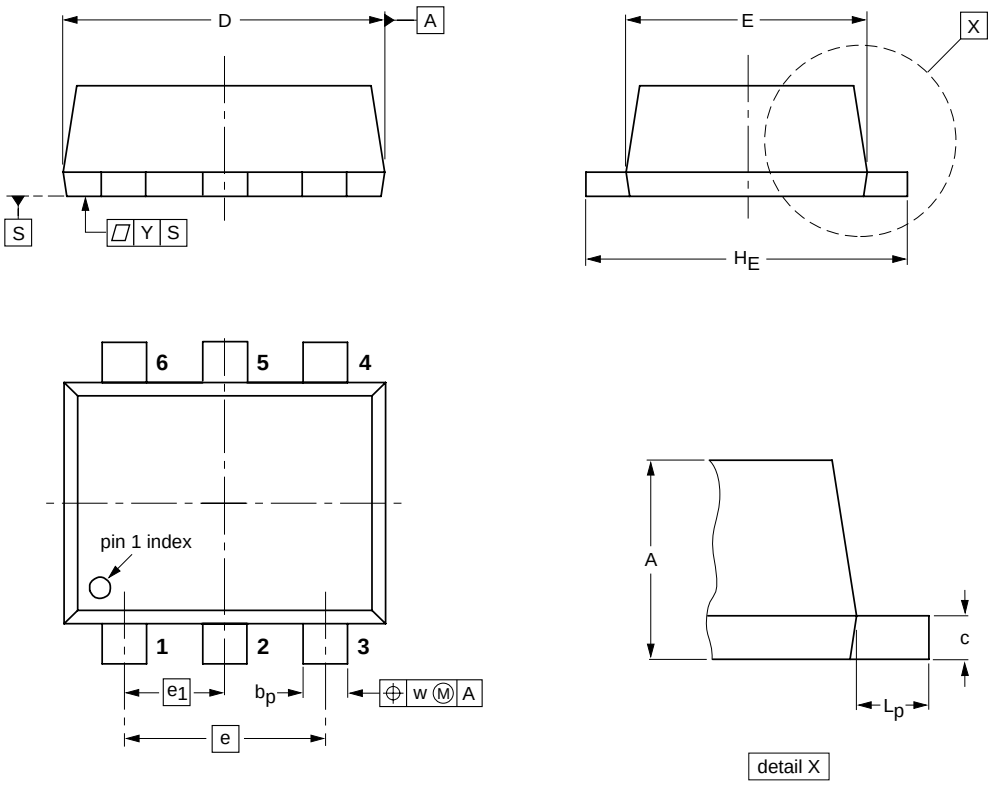


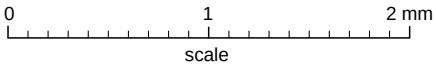
TR2 (PNP); I_C/I_B = 20.
(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

Fig.11 Collector-emitter saturation voltage as a function of collector current; typical values.

PACKAGE OUTLINE

Plastic surface mounted package; 6 leads **SOT666**





DIMENSIONS (mm are the original dimensions)

UNIT	A	b_p	c	D	E	e	e_1	H_E	L_p	w	y
mm	0.6 0.5	0.27 0.17	0.18 0.08	1.7 1.5	1.3 1.1	1.0	0.5	1.7 1.5	0.3 0.1	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT666						~~01-01-04~~ 01-08-27

DATA SHEET STATUS

DOCUMENT STATUS[1]	PRODUCT STATUS[2]	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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